





N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C		
60V	7.5Ω @ V _{GS} = 5V	210mA		

Description

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

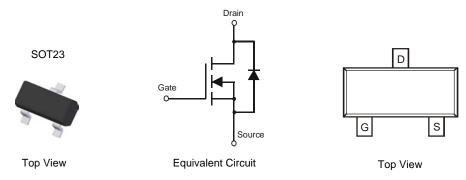
- Motor Control
- Power Management Functions

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Notes 3 & 4)
- Qualified to AEC-Q101 standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



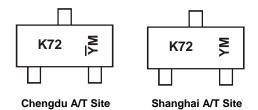
Ordering Information (Note 5)

Part Number	Compliance	Case	Packaging
2N7002-7-F	Standard	SOT23	3,000/Tape & Reel
2N7002-13-F	Standard	SOT23	10,000/Tape & Reel
2N7002Q-7-F	Automotive	SOT23	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Product manufactured with Date Code V12 (week 50, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V12 are built with Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



K72 = Product Type Marking Code
YM = Date Code Marking for SAT (S

 \underline{YM} = Date Code Marking for SAT (Shanghai Assembly/ Test site) \underline{YM} = Date Code Marking for CAT (Chengdu Assembly/ Test site) \underline{Y} or \underline{Y} = Year (ex: A = 2013)

M = Month (ex: 9 = September)

Date Code Kev

Date Code N	.ey															
Year	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	N	Р	R	S	Т	J	V	W	Χ	Υ	Z	Α	В	С	D	Е
Month	Jan	F	eb	Mar	Apr	M	lay	Jun	Jul	Α	ug	Sep	Oct	N-	ov	Dec
Code	1		2	3	4		5	6	7		8	9	0	1	V	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	60	V
Drain-Gate Voltage R _{GS} ≤ 1.0MΩ			V_{DGR}	60	V
Gate-Source Voltage		Continuous Pulsed	V _{GSS}	±20 ±40	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	$T_A = +25$ °C $T_A = +85$ °C $T_A = +100$ °C	I _D	170 120 105	mA
Continuous Drain Current (Note 7) V _{GS} = 10V	Steady State	$T_A = +25$ °C $T_A = +85$ °C $T_A = +100$ °C	I _D	210 150 135	mA
Maximum Body Diode Forward Current (Note 7)		oulsed ntinuous	I _S	0.5 2	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	ı	I _{DM}	800	mA	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Power Dissipation	(Note 6)	D-	370	mW	
Total Fower Dissipation	(Note 7)	P _D	540		
Thermal Desistance, Junction to Ambient	(Note 6)	2	348		
Thermal Resistance, Junction to Ambient	(Note 7)	R _{0JA}	241	°C/W	
Thermal Resistance, Junction to Case	(Note 7)	R _{0JC}	91		
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C	

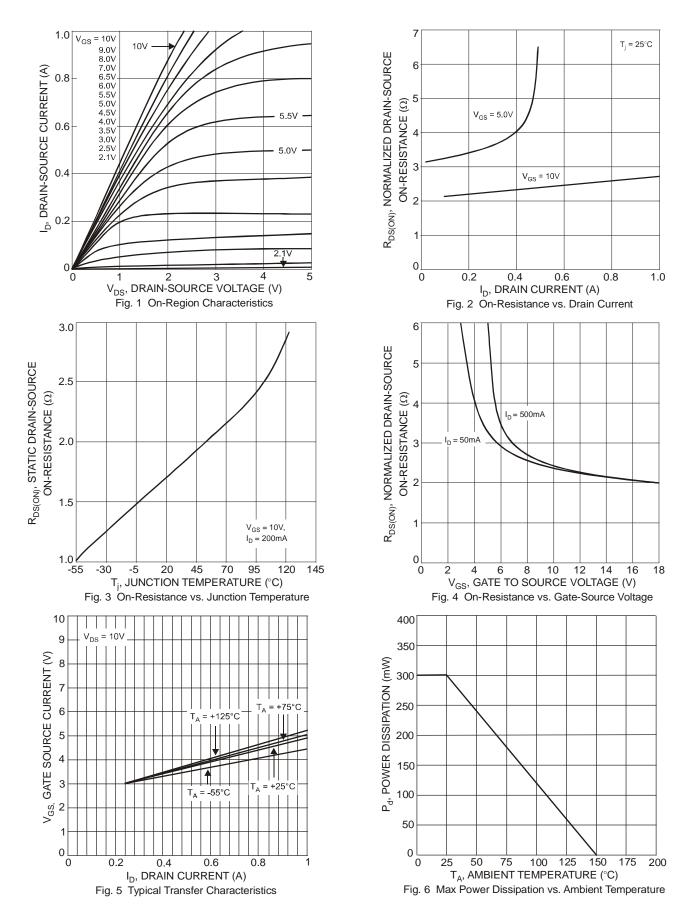
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage		BV _{DSS}	60	70	_	V	$V_{GS} = 0V, I_{D} = 10\mu A$
Zero Gate Voltage Drain Current	@ T _C = +25°C @ T _C = +125°C	I _{DSS}	_	_	1.0 500	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Body Leakage	-	I _{GSS}		_	±10	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						•	
Gate Threshold Voltage		$V_{GS(th)}$	1.0		2.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
Static Drain-Source On-Resistance	@ T _J = +25°C @ T _J = +25°C @ T _J = +125°C	R _{DS(ON)}	_	3.2 — 4.4	7.5 5.0 13.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$ $V_{GS} = 10V, I_D = 0.5A$ $V_{GS} = 10V, I_D = 0.5A$
On-State Drain Current		I _{D(ON)}	0.5	1.0	_	Α	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance		grs	80	_	_	mS	$V_{DS} = 10V, I_{D} = 0.2A$
Diode Forward Voltage		V _{SD}	_	0.78	1.5	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS (Note 9)						•	
Input Capacitance		C_{iss}		22	50	pF	\\ O5\\\\\ O\\
Output Capacitance		Coss		11	25	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance		C_{rss}		2.0	5.0	pF	1 = 1.000112
Gate resistance		R_{g}	_	120	_	Ω	$V_{DS} = 0V, V_{GS} = 0V,$ f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)		Qg	_	223	_		
Gate-Source Charge		Q _{gs}	_	82	_	рС	$V_{DS} = 10V, I_D = 250mA$
Gate-Drain Charge		Q_{gd}	_	178	_		
SWITCHING CHARACTERISTICS (Note 9)							
Turn-On Delay Time		t _{D(on)}	_	2.8	_		\/ 20\/ I 0.2A
Turn-On Rise Time	Turn-On Rise Time		_	3.0	_	ns	$V_{DD} = 30V$, $I_D = 0.2A$, $R_L = 150\Omega$, $V_{GEN} = 10V$,
Turn-Off Delay Time		t _{D(off)}		7.6	_	$R_{\text{GEN}} = 15002$, $V_{\text{GEN}} = 1$	
Turn-Off Fall Time		t _f	_	5.6	_		1.GEN - 2022

Notes:

- 6. Device mounted on FR-4 PCB, with minimum recommended pad layout
 7. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to product testing.

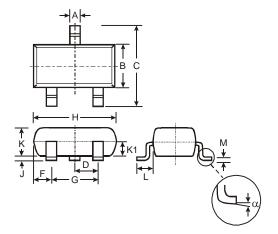






Package Outline Dimensions

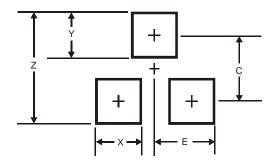
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.903	1.10	1.00					
K1	-	-	0.400					
L	0.45	0.61	0.55					
М	0.085	0.18	0.11					
α	0°	8°	-					
All Dimensions in mm								

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
Е	1.35



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